6th Generation CoolSiC[™]

IDH20G65C6



Table of Content

1	Maximum ratings	3
2	<u> </u>	
3	Electrical characteristics	4
3.1	Static characteristics	4
3.2	AC characteristics	4
4	Diagrams	5
5	Simplified forward characteristic	7
6	Package outlines	8



1 Maximum ratings

Table 3 Maximum ratings

Damana ahan	Ck	Values			11!4	/=	
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test condition	
	I_F	-	_	20		$T_C \le 135 ^{\circ}\text{C}, D = 1$	
Continuous forward current		-	-	22		$T_C \le 125 ^{\circ}\text{C}, D = 1$	
		-	-	41		$T_C \le 25$ °C, $D = 1$	
Surge-repetitive forward current, sine halfwave ¹	$I_{F,RM}$	-	-	87	A	$T_c = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$	
Surge non-repetitive forward		_	_	99		$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$	
current, sine halfwave	$I_{F,SM}$	_	_	79		$T_C = 150 ^{\circ}\text{C}, t_p = 10 \text{ms}$	
Non-repetitive peak forward current	I _{F,max}	-	_	780		$T_C = 25 ^{\circ}\text{C}, t_p = 10 \mu\text{s}$	
:24	(:2 -1+	-	-	49	A ² s	$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$	
i ² t value	∫ i²dt	_	_	31		$T_C = 150 ^{\circ}\text{C}, t_p = 10 \text{ms}$	
Repetitive peak reverse voltage	V_{RRM}	_	_	650	V	<i>T_c</i> = 25 °C	
Diode dv/dt ruggedness	dv/dt	_	_	150	V/ns	V _R = 0480 V	
Power dissipation	P _{tot}	_	_	108	W	$T_C = 25^{\circ}\text{C}, R_{thJC,max}$	
Operating and storage temperature	T_j T_{stg}	-55	-	175	°C	-	
Mounting torque	_	_	_	70	Ncm	M3 screw	

2 Thermal characteristics

Table 4 Thermal characteristics (PG-TO-220-2)

Downwater	Cymphol		Values		l lmit	Unit Note/Test condition
Parameter	Symbol	Min.	Тур.	Max.	Offic	
Thermal resistance, junction- case	R_{thJC}	_	0.8	1.3	12 /\\	-
Thermal resistance, junctionambient	R_{thJA}	_	_	62	K/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

¹ The surge-repetitive forward current test was performed with 1000 pulses (half-wave rectified sine with the 10 ms period).

Final Datasheet

3 Rev. 2.0, 2017-05-23



3 Electrical characteristics

3.1 Static characteristics

Table 5Static characteristics

Down makey	C: mah al		Values	Values Unit Note/Test condition			
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/ rest condition	
DC blocking voltage	V_{DC}	650	_	_		<i>T_j</i> = 25 °C	
Die de femuerd veltere	17	_	1.25	1.35	V	$I_F = 20 \text{ A}, T_j = 25 ^{\circ}\text{C}$	
Diode forward voltage	V_F	_	1.5	_		$I_F = 20 \text{ A}, T_j = 150 \text{ °C}$	
		_	2.0	67		$V_R = 420 \text{ V}, T_j = 25 \text{ °C}$	
Reverse current	I_R	_	66	_	μΑ	$V_R = 420 \text{ V}, T_j = 125 \text{ °C}$	
		_	153	_		$V_R = 420 \text{ V}, T_j = 150 \text{ °C}$	

3.2 AC characteristics

Table 6 AC characteristics

Devementor	Complete		Values		l lmit	Note/Test Condition
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test Condition
Total capacitive charge	Q_c	_	26.8	_	nC	V_R = 400 V, T_j = 150 °C, di/dt = 200 A/ μ s, $I_F \le I_{F,MAX}$
		_	970	_		$V_R = 1 \text{ V, } f = 1 \text{ MHz,}$ $T_j = 25 \text{ °C}$
Total capacitance	С	_	57	_	pF	V_R = 300 V, f = 1 MHz, T_j = 25 °C
		_	55	_		V_R = 600 V, f = 1 MHz, T_j = 25 °C



4 Diagrams

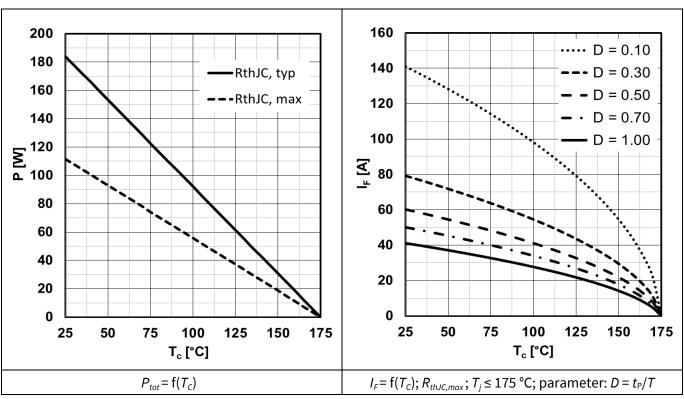


Figure 1 Power dissipation

Figure 2 Max. forward current

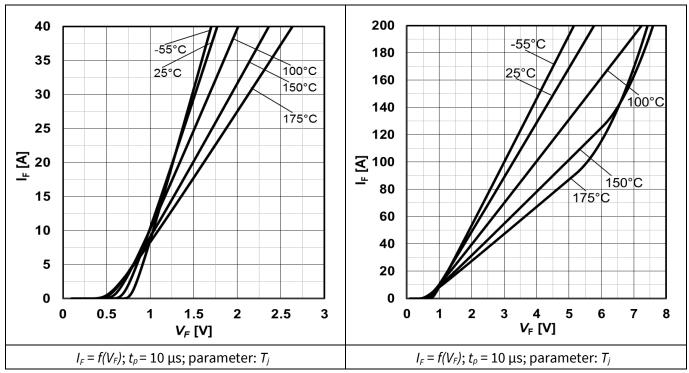


Figure 3 Typ. forward characteristics

Figure 4 Typ. forward characteristics in surge current



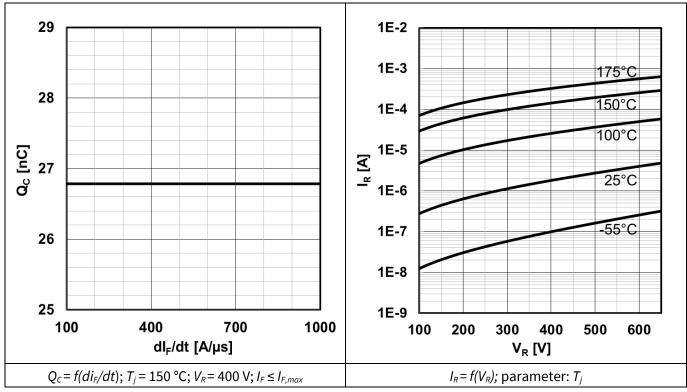


Figure 5 Typ. cap. charge vs. current slope

Figure 6 Typ. reverse current vs. reverse voltage

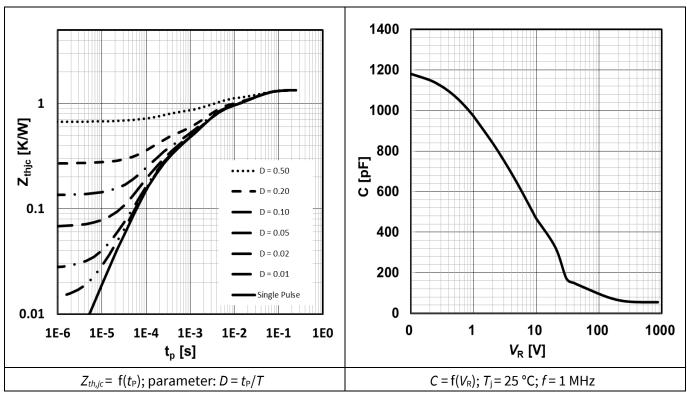


Figure 7 Max. transient thermal impedance

Figure 8 Typ. capacitance vs. reverse voltage



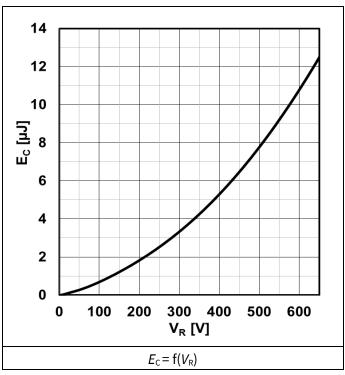


Figure 9 Typ. capacitance stored energy

5 Simplified forward characteristic

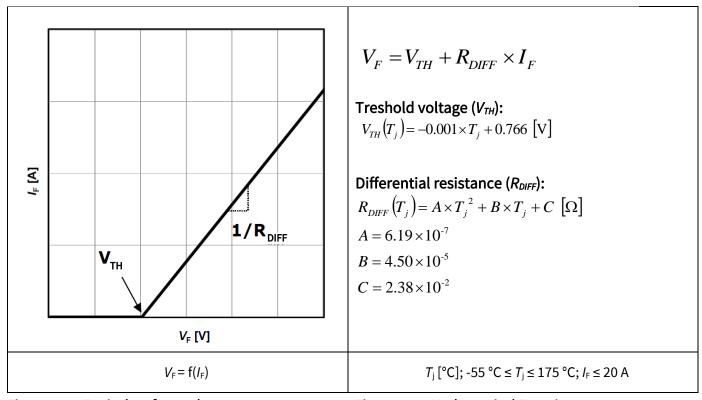


Figure 10 Equivalent forward current curve

Figure 11 Mathematical Equation



6 Package outlines

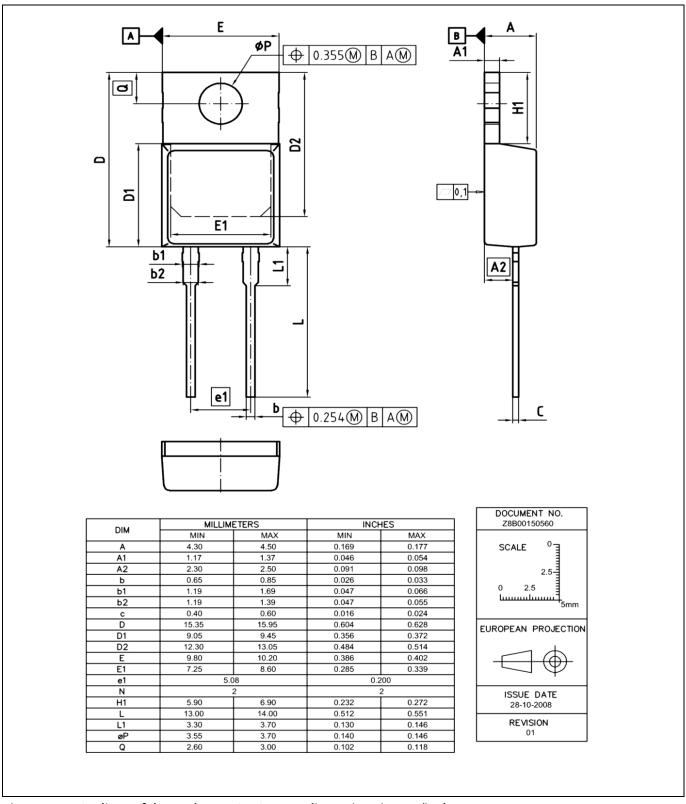


Figure 12 Outlines of the package PG-TO220-2, dimensions in mm/inches

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Revision History

Major changes since the last revision

Revision	Date	Subject (major changes since last revision)
2.0	2017-05-23	Release of final version

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